



OPEN

# Author Correction: Mechanism understanding in cryo atomic layer etching of SiO<sub>2</sub> based upon C<sub>4</sub>F<sub>8</sub> physisorption

G. Antoun, T. Tillocher, P. Lefauchaux, J. Faguet, K. Maekawa &amp; R. Dussart

Correction to: *Scientific Reports* <https://doi.org/10.1038/s41598-020-79560-z>, published online 11 January 2021

The original version of this Article contained an error in the Results section, under the subheading ‘Temperature dependency’ where

“From Eq. (1) and the values obtained with the curve fit, the values of  $t_d^0$  and  $E_d$  were determined to be respectively,  $1 \times 10^{-11}$  s and  $17 \text{ kJ mol}^{-1}$  (0.18 eV).”

now reads:

“From Eq. (1) and the values obtained with the curve fit, the values of  $t_d^0$  and  $E_d$  were determined to be respectively,  $1 \times 10^{-11}$  s and 0.406 eV (39.1  $\text{kJ mol}^{-1}$ ).”

The original Article has been corrected.



**Open Access** This article is licensed under a Creative Commons Attribution 4.0 International License, which permits use, sharing, adaptation, distribution and reproduction in any medium or format, as long as you give appropriate credit to the original author(s) and the source, provide a link to the Creative Commons licence, and indicate if changes were made. The images or other third party material in this article are included in the article's Creative Commons licence, unless indicated otherwise in a credit line to the material. If material is not included in the article's Creative Commons licence and your intended use is not permitted by statutory regulation or exceeds the permitted use, you will need to obtain permission directly from the copyright holder. To view a copy of this licence, visit <http://creativecommons.org/licenses/by/4.0/>.

© The Author(s) 2022